

Request Information Permalink

This technology is currently not available for licensing

Tech ID: 29182

ADDITIONAL TECHNOLOGIES BY THESE INVENTORS

- ▶ Vertical Cavity Surface-Emitting Lasers with Continuous Wave Operation
- ▶ Eliminating Misfit Dislocations with In-Situ Compliant Substrate Formation
- ▶ III-Nitride-Based Vertical Cavity Surface Emitting Laser (VCSEL) with a Dielectric P-Side Lens
- ▶ Enhanced Light Extraction LED with a Tunnel Junction Contact Wafer Bonded to a Conductive Oxide
- ▶ Improved Reliability & Enhanced Performance of III-Nitride Tunnel Junction Optoelectronic Devices
- (In,Ga,AI)N Optoelectronic Devices with Thicker Active Layers for Improved Performance
- ► Thermally Stable, Laser-Driven White Lighting Device
- ▶ III-Nitride Tunnel Junction LED with High Wall Plug Efficiency
- Novel Multilayer Structure for High-Efficiency UV and Far-UV Light-Emitting Devices
- ► A Method To Lift-Off Nitride Materials With Electrochemical Etch
- ► High-Intensity Solid State White Laser Diode
- ▶ Nitride Based Ultraviolet LED with an Ultraviolet Transparent Contact
- ▶ High-Efficiency and High-Power III-Nitride Devices Grown on or Above a Strain Relaxed Template
- ▶ III-Nitride Based VCSEL with Curved Mirror on P-Side of the Aperture



in